

IS450

OPIC Light Detector with Built-in Signal Processing Circuit for Light Modulation System

■ Features

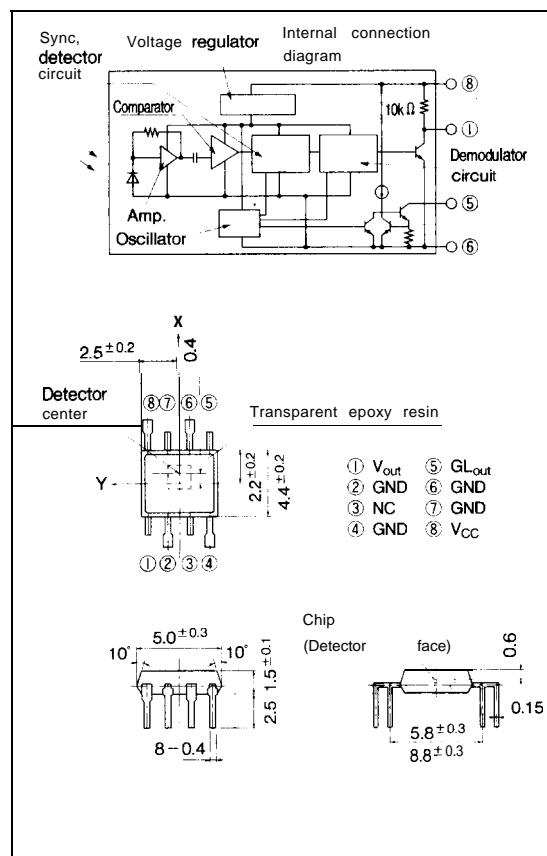
1. Impervious to external disturbing lights due to light modulation system
2. Built-in pulse driver circuit and sync. detector circuit on the emitter side
3. A wide range of operating supply voltage (V_{CC}: 4.5 to 9 V)
4. 1.5mm thin dual-in-line package

■ Applications

1. Optoelectronic switches
2. Copiers, printers, facsimiles

■ Outline Dimensions

(Unit : mm)



* "OPIC" (Optical IC) is a trademark of the SHARP Corporation.
An OPIC consists of a light-detecting element and signal-processing circuit integrated onto a single chip.

■ Absolute Maximum Ratings (Ta= 25°C)

Parameter	Symbol	Rating	Unit
Supply voltage	V _{CC}	-0.5 to 9	V
Output	Output voltage	V _O	V
	Output current	I _O	mA
* ¹ GL output	V _{GL}	9	V
Power dissipation	P	150	mW
Operating temperature	T _{opr}	-25 to +60	°C
Storage temperature	T _{ste}	-40 to +85	°C
* ² Soldering temperature	T _{sot}	260	°C

*1 Applies to GL_{out} terminal.

*2 For 5 seconds at the position of 1mm from the bottom face of resin package.

■ Electro-optical Characteristics

(V_{CC}=5V, Ta=25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Operating supply voltage	V _{CC}		4.5	—	9	v
Supply current	I _{CC}	V _O , GL _{out} terminals shall be opened.	—	3.5	7.0	mA
output	Low level output voltage	V _{OL}	I _{OL} =16mA, E _{VP} =500lx, E _{VD} =0 *3	—	0.15	0.35
	High level output voltage	V _{OH}	E _{VP} =E _{VD} =O *3	4.95	—	—
	Output short circuit current	I _{OS}	E _{VP} =E _{VD} =O *3	0.25	0.5	1.0
GL output	Low level output current	I _{GL}	V _{GL} =1.2V	40	55	mA
	*4Pulse cycle	t _p		70	130	220
	*4Pulse width	t _w		4.4	8	13.7
*5 "Low→High" threshold irradiance	E _{ePLH}	E _{eD} =0, Light emitting diode (λ _P =940nm) *3 *6	—	0.5	2.1	μW/mm ²
* "High→Low" threshold irradiance	E _{ePHL}	—	—	0.8	2.2	μW/mm ²
Hysteresis	E _{ePLH} /E _{ePHL}		0.45	0.65	0.95	—
Response "High→Low" propagation delay time	t _{pHL}	*6	—	400	670	μs
"Low→High" propagation delay time	t _{pLH}	*6	—	400	670	μs
* External disturbing light illuminance	E _{VDX}	*5E _{en} =6.6 μW/mm ² , λP=940nm	750	3600	—	lx

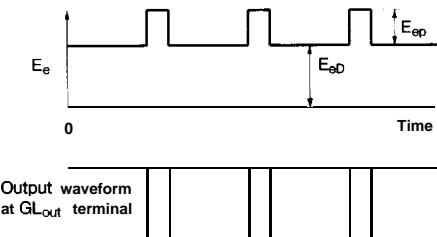
*3 E_{ep} represents illuminance of signal light in sync with the low level timing of output at GL_{out} terminal.Light source : Infrared light emitting diode (λ_P=940nm)E_{eD} represents illuminance of DC light. For detail, see Fig. 1. Note that the light source in CIE standard light**Fig. 1**(Note) Fig. 1 shows the output voltage waveform at GL_{out} terminal with IS450 connected as shown in Fig. 3.*4 Pulse cycle (t_o), pulse width (t_w) are defined as shown in Fig. 2.The waveform shown in Fig. 2 is the output voltage waveform at GL_{out} terminal with S450 connected as shown in Fig. 3.

Fig. 2

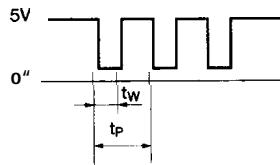
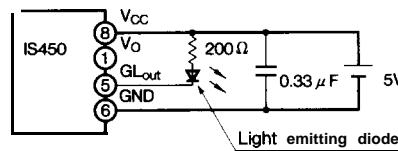


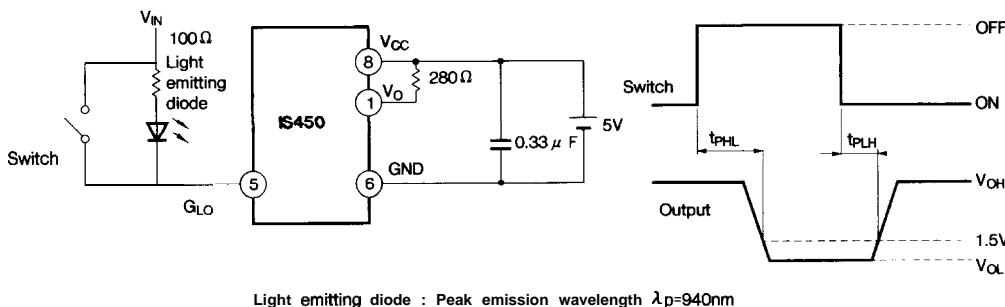
Fig. 3



*5 Defined as E_{ep} that causes the output to go "Low \rightarrow High" (or "High \rightarrow Low").

*6 Test circuit for response time, threshold irradiance is shown in Fig.4.

Fig. 4



Light emitting diode : Peak emission wavelength $\lambda_p=940\text{nm}$

*7 EVDX :Defined as the EVD at the limit of normal operation range

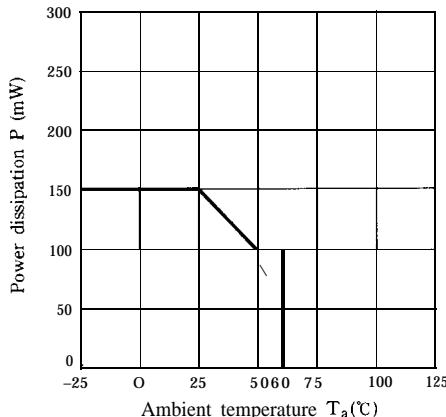
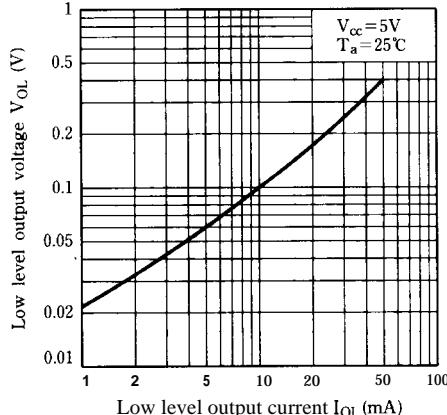
Fig. 5 Power Dissipation vs.
Ambient TemperatureFig. 6 Low Level Output Voltage vs.
Low Level Output Current

Fig. 7 Low Level Output Voltage vs. Ambient Temperature

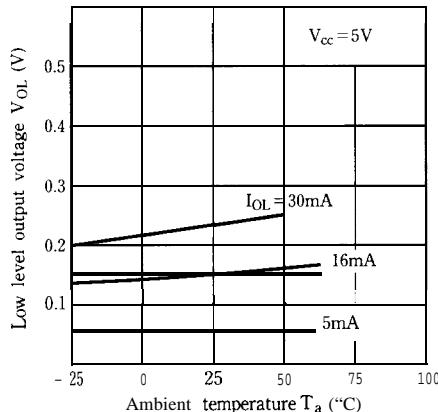


Fig. 8 Supply Current vs. Supply Voltage

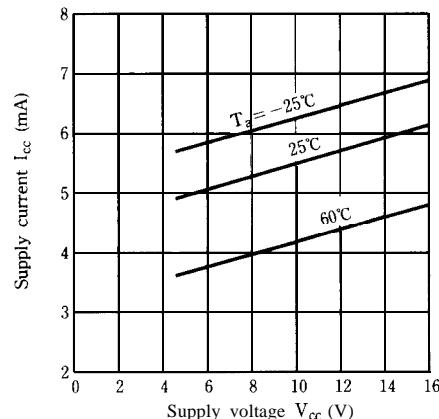


Fig. 9 Low Level Output Current vs. Supply voltage

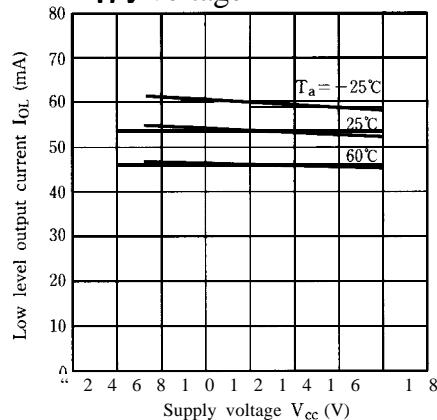


Fig.10 Sensitivity Diagram ($T_a=25^\circ C$)

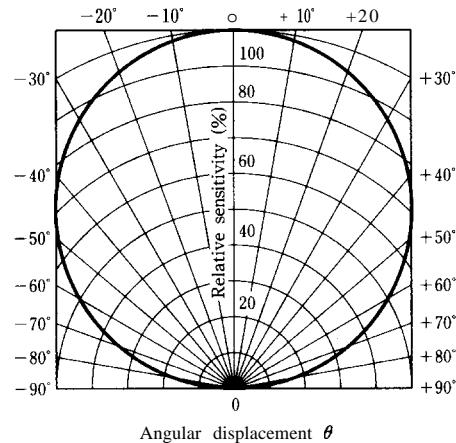
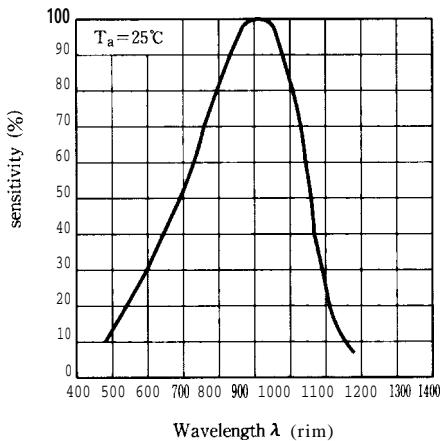
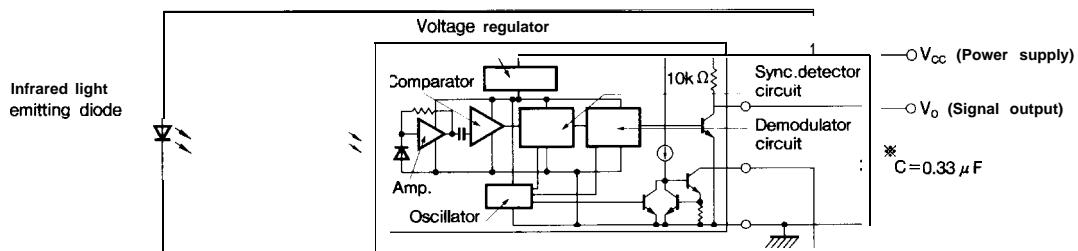


Fig.11 Spectral Sensitivity



■ Basic Circuit



* In order to stabilize power supply line, connect a by-pass capacitor of $0.33 \mu F$ or more between V_{cc} and GND near the device

● Please refer to the chapter "Precautions for Use" (Page 78 to 93)